

40 V N-channel Trench MOSFET

2 April 2019

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	40	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	4.8	А
Static chara	octeristics		•				
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 4.8 A; T _j = 25 °C		-	23	30	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



5. Pinning information

Table 2. F	Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	G	gate	3	D				
2	S	source						
3	D	drain	1 2 TO-236AB (SOT23)	G G S 017aaa255				

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMV30ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV30ENEA	R6%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

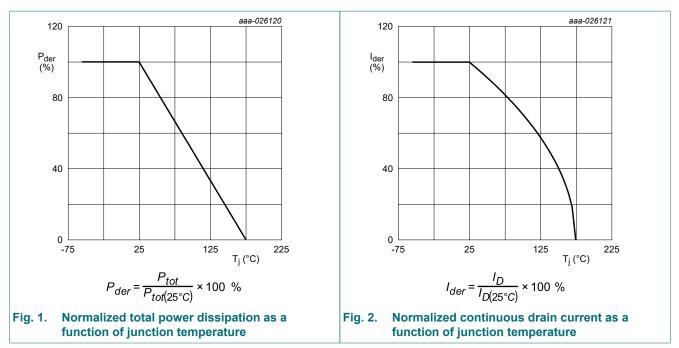
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	40	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	4.8	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	3.4	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	19	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	710	mW
			[1]	-	1.3	W
		T _{sp} = 25 °C		-	8.3	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain	diode					
Is	source current	T _{amb} = 25 °C	[1]	-	1.3	А
ESD maximu	m rating				-	
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Avalanche ru	ggedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ T_{j(init)} = 25 \text{ °C}; I_D = 0.83 \text{ A}; \text{ DUT in}$ avalanche (unclamped)		-	16.7	mJ

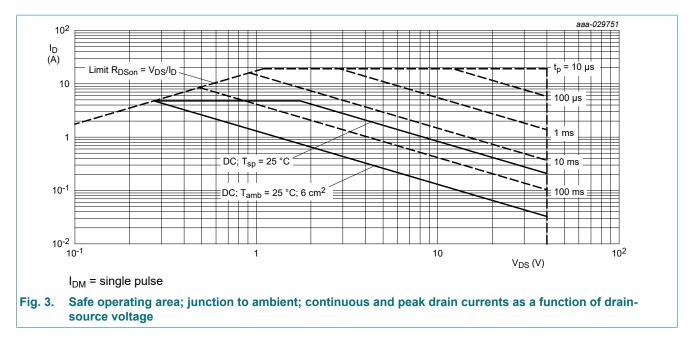
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



40 V N-channel Trench MOSFET

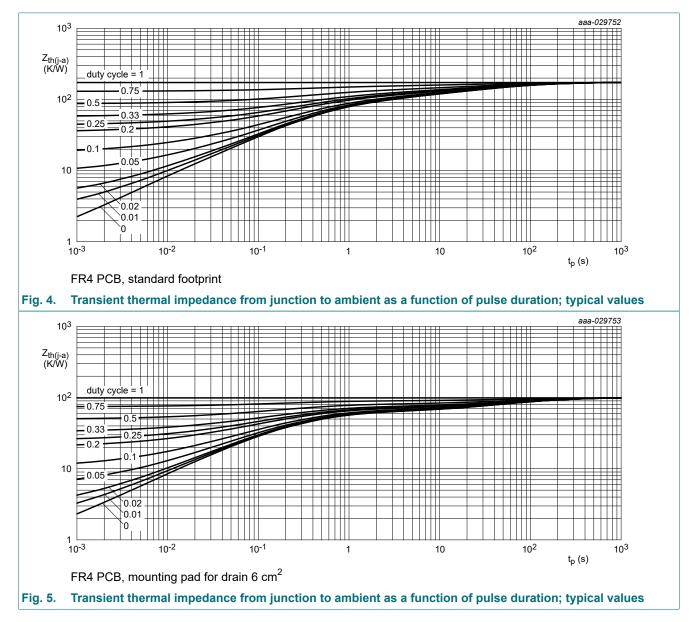


9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	175	210	K/W
	junction to ambient		[2]	-	95	115	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	13	18	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

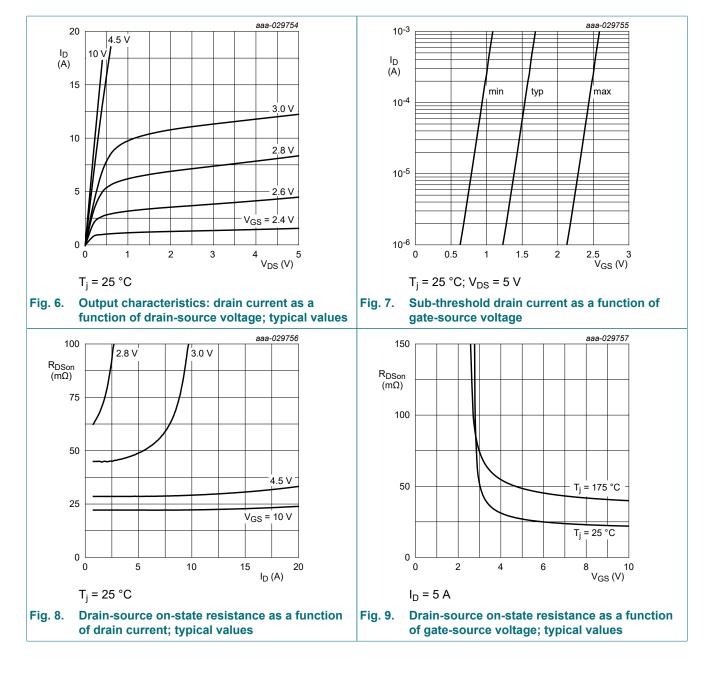
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



10. Characteristics

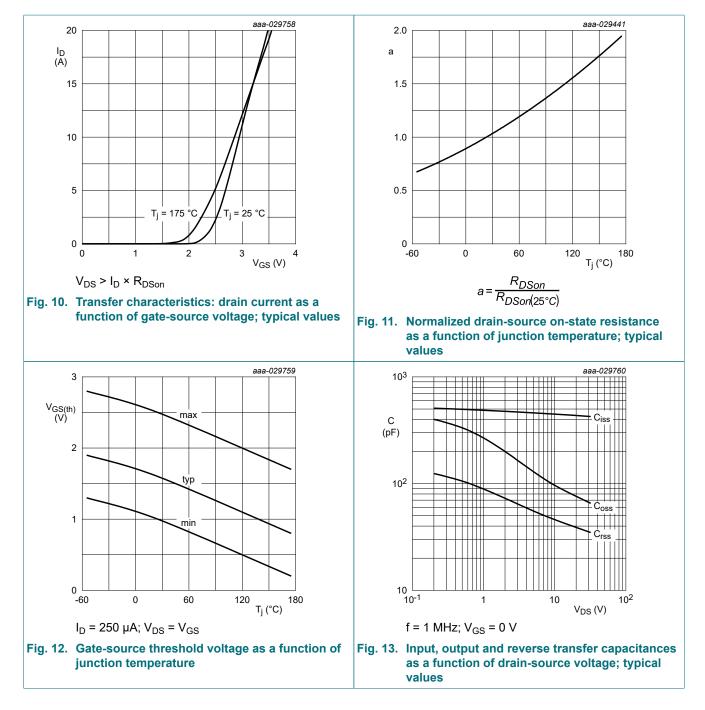
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	1	1.6	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 4.8 A; T _j = 25 °C	-	23	30	mΩ
	resistance	V _{GS} = 10 V; I _D = 4.8 A; T _j = 175 °C	-	44	57	mΩ
		V _{GS} = 4.5 V; I _D = 4.1 A; T _j = 25 °C	-	30	40	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 3 A; T _j = 25 °C	-	19	-	S
R _G	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	aracteristics	1				
Q _{G(tot)}	total gate charge	V _{DS} = 20 V; I _D = 4.8 A; V _{GS} = 10 V;	-	7.8	11.7	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.2	-	nC
Q _{GD}	gate-drain charge	1	-	1.6	-	nC
C _{iss}	input capacitance	V _{DS} = 20 V; f = 1 MHz; V _{GS} = 0 V;	-	440	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	76	-	pF
C _{rss}	reverse transfer capacitance	-	-	39	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 20 V; I _D = 4.8 A; V _{GS} = 10 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	2	-	ns
t _{d(off)}	turn-off delay time	1 1	-	20	-	ns
t _f	fall time	1 -	-	33	-	ns
Source-drai	n diode					
V _{SD}	source-drain voltage	I _S = 1.3 A; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 1.3 A; dI _S /dt = -100 A/µs;	-	11	-	ns
Q _r	recovered charge	V _{GS} = 0 V; V _{DS} = 20 V; T _j = 25 °C	-	4	-	nC

40 V N-channel Trench MOSFET

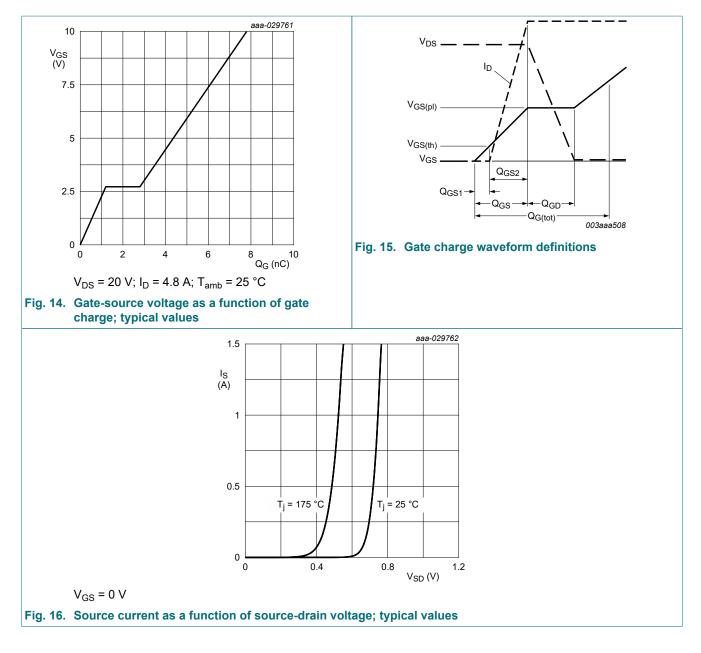


Product data sheet

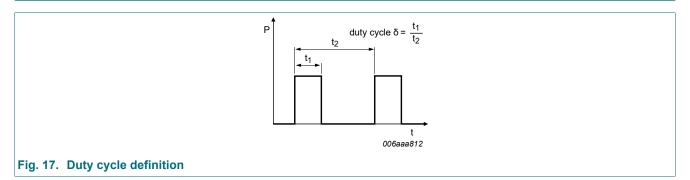
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11. Test information

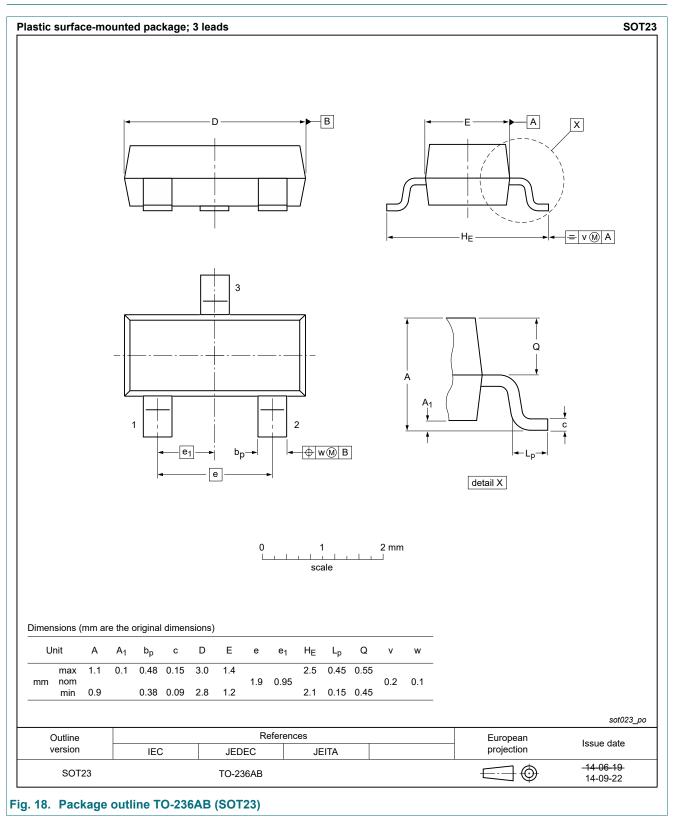


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

40 V N-channel Trench MOSFET

12. Package outline



13. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMV30ENEA v.1	20190402	Product data sheet	-	-		

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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40 V N-channel Trench MOSFET

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40 V N-channel Trench MOSFET

Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Characteristics	6
11. Test information	10
12. Package outline	11
13. Revision history	12
14. Legal information	

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Product data sheet



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